

TISP4072F3LM THRU TISP4082F3LM, TISP4125F3LM THRU TISP4180F3LM, TISP4240F3LM THRU TISP4380F3LM

BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

TISP4xxxF3LM Overvoltage Protector Series

Device Symbol

Ion-Implanted Breakdown Region Precise and Stable Voltage Low Voltage Overshoot under Surge

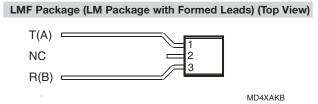
Device	V _{DRM} V	V _(BO)
'4072	58	72
'4082	66	82
'4125	100	125
'4150	120	150
'4180	145	180
'4240	180	240
'4260	200	260
'4290	220	290
'4320	240	320
'4380	270	380

Rated for International Surge Wave Shapes

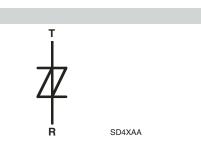
Waveshape Standard		I _{TSP}
Waveshape	Otandard	Α
10/160 μs	FCC Part 68	60
0.5/700 μs	I3124	38
10/700 μs	ITU-T K.20/21	50
10/560 μs	FCC Part 68	45
10/1000 μs	REA PE-60	35



T(A) 1 2 3 3 MD4XAT NC - No internal connection on pin 2



NC - No internal connection on pin 2



Terminals T and R correspond to the alternative line designators of A and B

Description

These devices are designed to limit overvoltages on the telephone line. Overvoltages are normally caused by a.c. power system or lightning flash disturbances which are induced or conducted on to the telephone line. A single device provides 2-point protection and is typically used for the protection of 2-wire telecommunication equipment (e.g. between the Ring to Tip wires for telephones and modems). Combinations of devices can be used for multi-point protection (e.g. 3-point protection between Ring, Tip and Ground).

The protector consists of a symmetrical voltage-triggered bidirectional thyristor. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. The high crowbar holding current prevents d.c. latchup as the diverted current subsides.

How To Order

Device	Package	Carrier	For Standard Termination Finish Order As	For Lead Free Termination Finish Order As
	Straight Lead DO-92 (LM)	Bulk Pack	TISP4xxxF3LM	TISP4xxxF3LM-S
TISP4xxxF3LM	Straight Lead DO-92 (LIVI)	Tape and Reeled	TISP4xxxF3LMR	TISP4xxxF3LMR-S
	Formed Lead DO-92 (LMF)	Tape and Reeled	TISP4xxxF3LMFR	TISP4xxxF3LMFRS

Insert xxx value corresponding to protection voltages of 072, 082, 125 etc.



Description (continued)

This TISP4xxxF3LM range consists of ten voltage variants to meet various maximum system voltage levels (58 V to 270 V). They are guaranteed to voltage limit and withstand the listed international lightning surges in both polarities. These protection devices are supplied in a DO-92 (LM) cylindrical plastic package. The TISP4xxxF3LM is a straight lead DO-92 supplied in bulk pack and on tape and reeled. The TISP4xxxF3LMF is a formed lead DO-92 supplied only on tape and reeled.

Absolute Maximum Ratings, T_A = 25 °C (Unless Otherwise Noted)

Rating			Value	Unit
Repetitive peak off-state voltage (0 °C < T _J < 70 °C)	4072 4082 4125 4150 4180 4240 4260 4290 4320	Symbol V _{DRM}	± 58 ± 66 ± 100 ± 120 ± 145 ± 180 ± 200 ± 220 ± 240	V
Non-repetitive peak on-state pulse current (see Notes 1, 2 and 3) 2/10 μs (FCC Part 68, 2/10 μs voltage wave shape) excluding '4072 - '4082 8/20 μs (ANSI C62.41, 1.2/50 μs voltage wave shape) excluding '4072 - '4082 10/160 μs (FCC Part 68, 10/160 μs voltage wave shape) 5/200 μs (VDE 0433, 2 kV, 10/700 μs voltage wave shape) 0.2/310 μs (I3124, 1.5 kV, 0.5/700 μs voltage wave shape) 5/310 μs (ITU-T K.20/21, 1.5 kV, 10/700 μs voltage wave shape) 5/310 μs (FTZ R12, 2 kV, 10/700 μs voltage wave shape) 10/560 μs (FCC Part 68, 10/560 μs voltage wave shape) 10/1000 μs (REA PE-60, 10/1000 μs voltage wave shape) 2/10 μs (FCC Part 68, 2/10 μs voltage wave shape) '4072 - '4082 only 8/20 μs (ANSI C62.41, 1.2/50 μs voltage wave shape) '4072 - '4082 only	4380	I _{TSP}	± 270 175 120 60 50 38 38 50 45 35 80 70	Α
Non-repetitive peak on-state current (see Notes 2 and 3) 50/60 Hz, 1 s		I _{TSM}	4	Α
Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 38 A		di _T /dt	250	A/μs
Junction temperature		T _J	-40 to +150	°C
Storage temperature range		T _{stg}	-55 to +150	°C

NOTES: 1. Initially the TISP must be in thermal equilibrium with 0 $^{\circ}C < T_{J} < 70 \ ^{\circ}C.$

2. The surge may be repeated after the TISP returns to its initial conditions.

3. Above 70 $^{\circ}\text{C}$, derate linearly to zero at 150 $^{\circ}\text{C}$ lead temperature.

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Electrical Characteristics for R and T Terminals, T_J = 25 $^{\circ}$ C (Unless Otherwise Noted)

	Parameter	Test Conditions		Min	Тур	Max	Unit
I _{DRM}	Repetitive peak off-	V _D = ±V _{DRM} , 0 °C < T _J < 70 °C				±10	μА
-DUM	state current	- Univip - C					r
			'4072			±72	
			'4082			±82	
			'4125			±125	
			'4150			±150	
V _(BO)	Breakover voltage	$dv/dt = \pm 250 \text{ V/ms}, R_{SOURCE} = 300 \Omega$	'4180			±180	V
(50)	· ·	COORDE	'4240			±240	
			'4260 '4260			±260	
			'4290 '4290			±290	
			'4320 '4320			±320	
			'4380 '4380			±380	
			'4072 '4082			±86	
			4082			±96 ±143	
	Impulse breakover voltage					±143 ±168	
		$dv/dt = \pm 1000 \text{ V/μs}, R_{SOURCE} = 50 \Omega$ $di/dt < 20 \text{ A/μs}$	'4150 '4180			±108	V
V _(BO)			4240			±130	
			4260			±207 ±287	
			4290			±317	
			·4320			±347	
			4380			±407	
I _(BO)	Breakover current	$dv/dt = \pm 250 \text{ V/ms}, R_{SOURCE} = 300 \Omega$		±0.15		±0.6	Α
V _T	On-state voltage	$I_T = \pm 5 \text{ A}, t_W = 100 \mu \text{s}$				±3	V
I _H	Holding current	$I_T = \pm 5 \text{ A, di/dt} = -/+30 \text{ mA/ms}$		±0.15			Α
dv/dt	Critical rate of rise of off-state voltage	Linear voltage ramp, Maximum ramp value < 0.85V _{DRM}		±5			kV/μs
I _D	Off-state current	$V_{D} = \pm 50 \text{ V}$				±10	μΑ
		$f = 100 \text{ kHz}, V_d = 1 \text{ V r.m.s.}, V_D = 0,$	'4072 - '4082		63	108	•
	Off-state capacitance	, u , b ,	'4125 - '4180		43	74	
C _{off}		f = 100 kHz, V _d = 1 V r.m.s., V _D = -50 V	'4240 - '4380		44	74	pF
			'4072 - '4082		25	40	
			'4125 - '4180		15	25	
			'4240 - '4380		11	20	

Thermal Characteristics

	Parameter	Test Conditions	Min	Тур	Max	Unit
R _{OJA}	Junction to free air thermal resistance	EIA/JESD51-3 PCB mounted in an EIA/ JESD51-2 enclosure			120	°C/W

Parameter Measurement Information

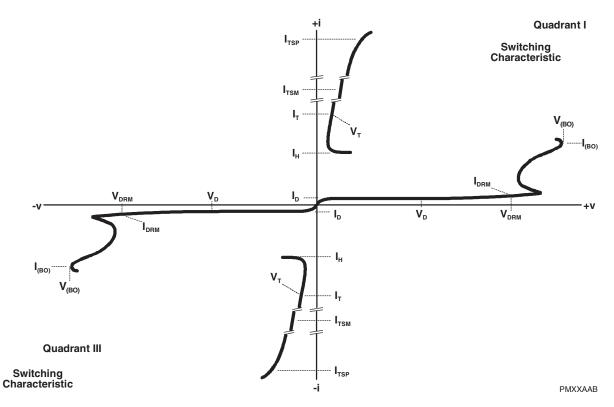
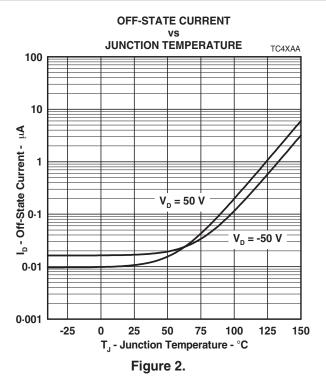


Figure 1. Voltage-Current Characteristic for R and T Terminals

All Measurements are Referenced to the T Terminal

Typical Characteristics



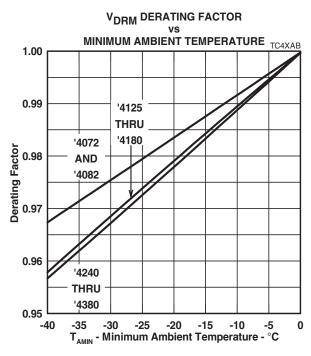
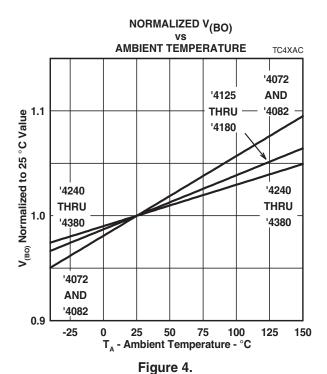
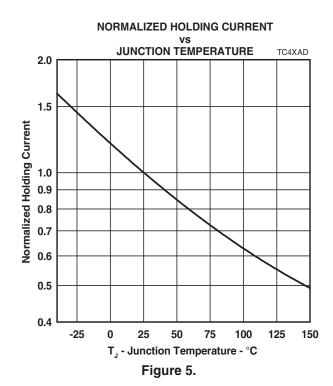


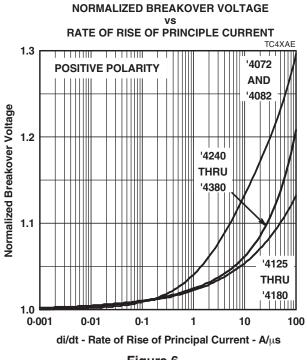
Figure 3.





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Typical Characteristics



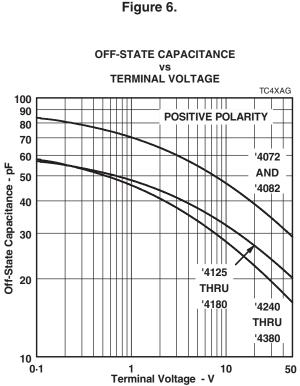
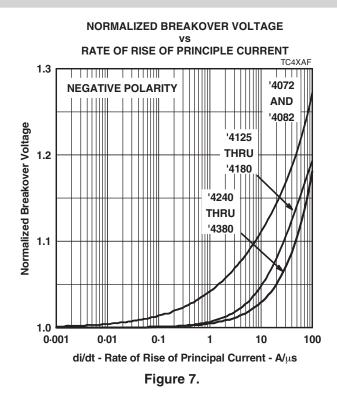
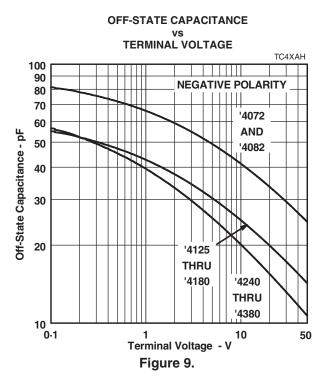


Figure 8.





Typical Characteristics

NON-REPETITIVE PEAK ON-STATE CURRENT vs CURRENT DURATION 10 Irsm(t) - Non-Repetitive Peak On-State Current - A 9 V_{GEN} = 600 Vrms, 50/60 Hz 8 $R_{GEN(t)} = 1.4*V_{GEN} / I_{TSM(t)}$ 7 6 5 3 2 0.1 10 100 1000 t - Current Duration - s

Figure 10.



MECHANICAL DATA

Device Symbolization Code

Devices will be coded as below.

Device	Symbolization Code
TISP4072F3	4072F3
TISP4082F3	4082F3
TISP4125F3	4125F3
TISP4150F3	4150F3
TISP4180F3	4180F3
TISP4240F3	4240F3
TISP4260F3	4260F3
TISP4290F3	4290F3
TISP4320F3	4320F3
TISP4380F3	4380F3

Carrier Information

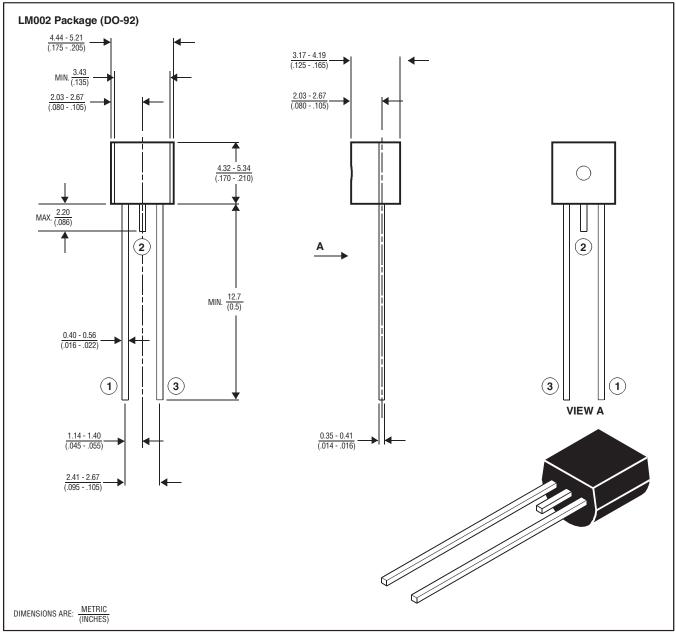
Devices are shipped in one of the carriers below. A reel contains 2,000 devices.

Package Type	Carrier	For Standard Termination Finish Order As	For Lead Free Termination Finish Order As
Straight Lead DO-92	Bulk Pack	TISP4xxxF3LM	TISP4xxxF3LM-S
Straight Lead DO-92	Tape and Reeled	TISP4xxxF3LMR	TISP4xxxF3LMR-S
Formed Lead DO-92	Tape and Reeled	TISP4xxxF3LMFR	TISP4xxxF3LMFRS

MECHANICAL DATA

LM002 (DO-92) 2-Pin Cylindrical Plastic Package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.

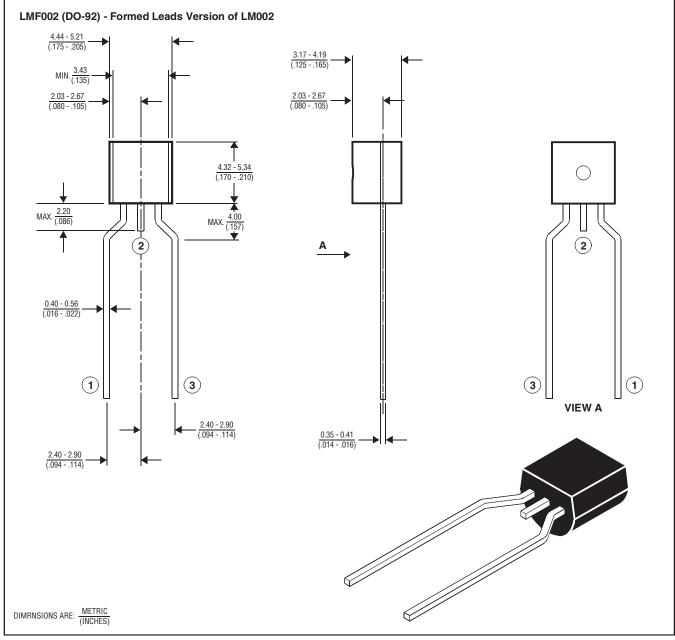


MD4XARA

MECHANICAL DATA

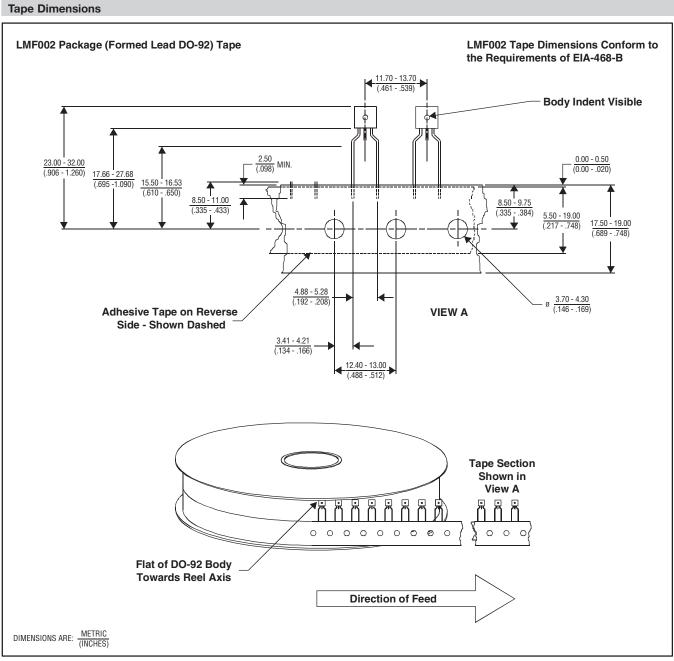
LM002 (DO-92) - Formed Leads Version - 2-Pin Cylindrical Plastic Package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



MD4XASA

MECHANICAL DATA



MD4XAQC

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